Detailed surface analysis of V-defects in GaN films on patterned silicon(111) substrates by metal–organic chemical vapour deposition. Corrigendum


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A label error has been found in Fig. 3(d) in the paper by Gao et al. (2019). The error is that ‘Terrace High GR’ should read ‘Terrace Low GR’. Here we publish the revised Fig. 3. This correction does not affect the text description in the paper.

Figure 3 (revised)
Schematic representation of the growth mode of a V-defect. (a) Original state, (b) normal growth, (c) formation of the V-defect and (d) filling up of the V-defect.

References